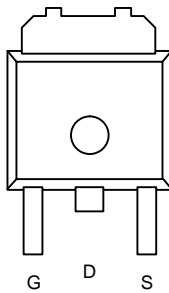


N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
200	0.180 at $V_{GS} = 10$ V	18
	0.255 at $V_{GS} = 4.5$ V	10

TO-252



Top View

FEATURES

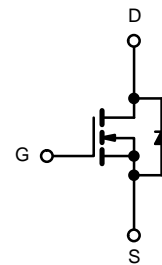
- DT-Trench Power MOSFET
- 100 % Rgand UIS Tested
- 175 °C Junction Temperature



RoHS
COMPLIANT

APPLICATIONS

- DC/DC Converters
- DC/AC Inverters
- Motor Drives



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	72	
Avalanche Current	I_{AS}	25	
Single Avalanche Energy ^a	E_{AS}	15.7	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	W
		$T_A = 25$ °C ^c	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	60	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.5	

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	200			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.2		3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 250	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 160 V, V _{GS} = 0 V			1	μA
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 160 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	18			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 8 A		0.180	0.220	Ω
		V _{GS} = 4.5 V, I _D = 6 A		0.255	0.315	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 6 A		20		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 160 V, V _{GS} = 0 V, f = 1 MHz		2260		pF
Output Capacitance	C _{oss}			685		
Reverse Transfer Capacitance	C _{rss}			40		
Total Gate Charge ^c	Q _g	V _{DS} = 160 V, V _{GS} = 10 V, I _D = 8 A		19.8	30	nC
Gate-Source Charge ^c	Q _{gs}			3.6		
Gate-Drain Charge ^c	Q _{gd}			4.1		
Gate Resistance	R _g	f = 1 MHz		2		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 160 V, R _L = 9.6 Ω I _D ≅ 8 A, V _{GEN} = 10 V, R _g = 1 Ω		8	16	ns
Rise Time ^c	t _r			11	20	
Turn-Off Delay Time ^c	t _{d(off)}			18	27	
Fall Time ^c	t _f			5	10	
Drain-Source Body Diode Ratings and Characteristics ^b T _C = 25 °C						
Continuous Current	I _S				18	A
Pulsed Current	I _{SM}				72	
Forward Voltage ^a	V _{SD}	I _F = 5.2 A, V _{GS} = 0 V		0.7	1.2	V
Reverse Recovery Time	t _{rr}			34	51	ns

Notes:

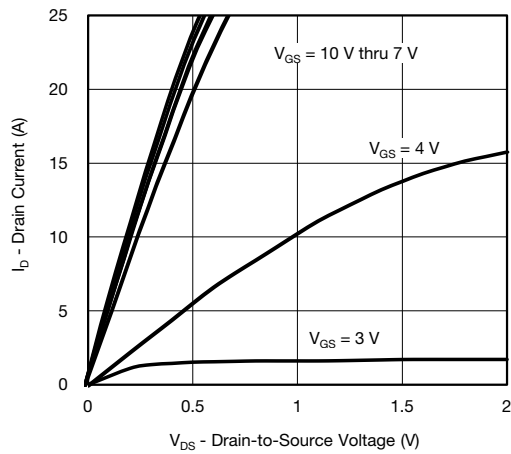
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

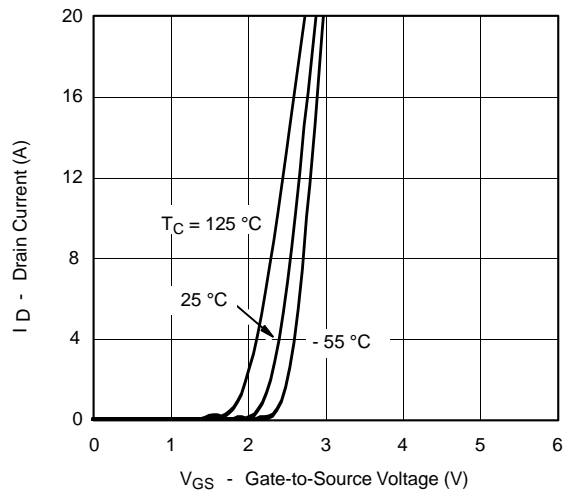
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

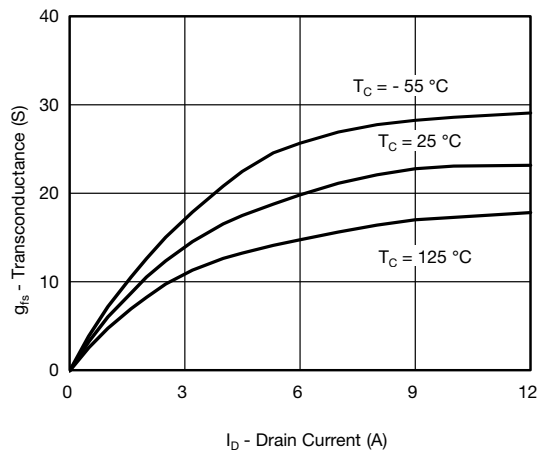
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



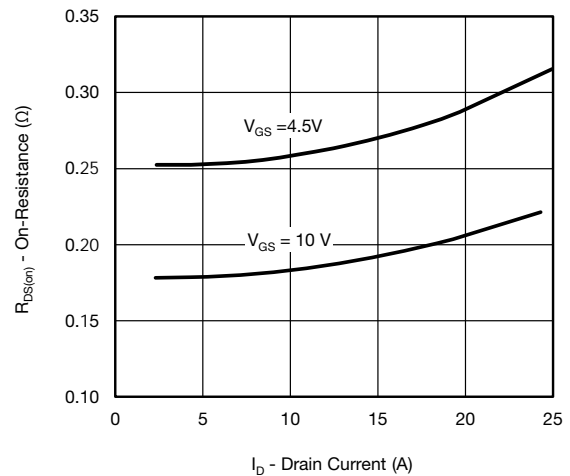
Output Characteristics



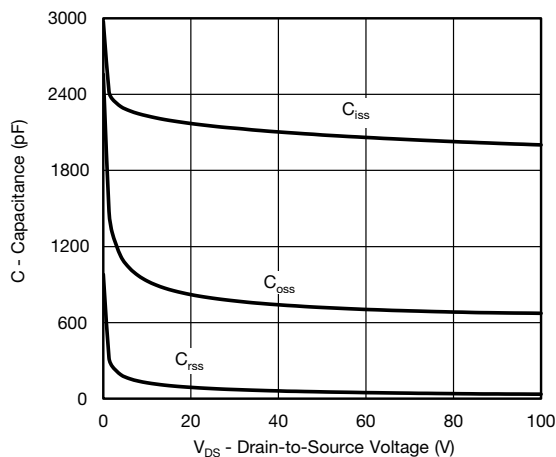
Transfer Characteristics



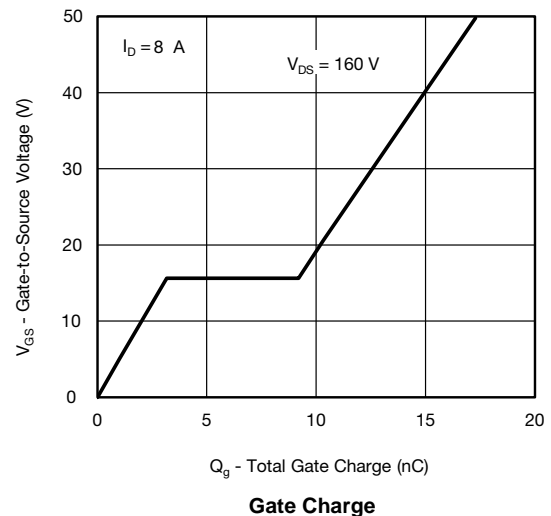
Transconductance



On-Resistance vs. Drain Current

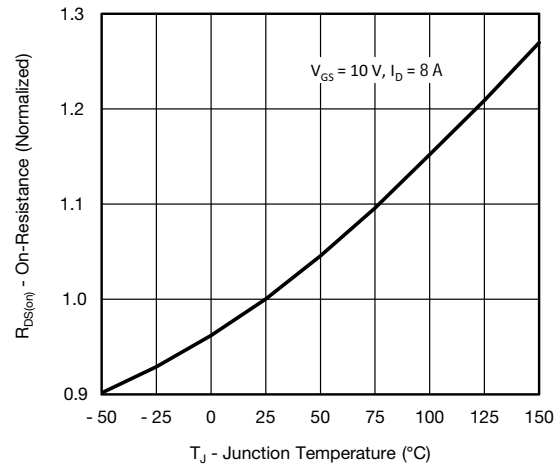
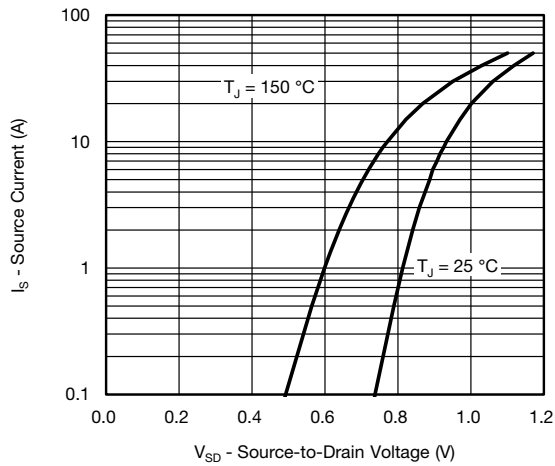


Capacitance

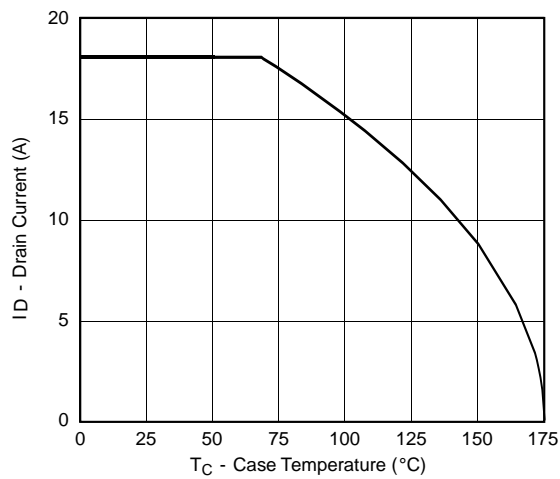


Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

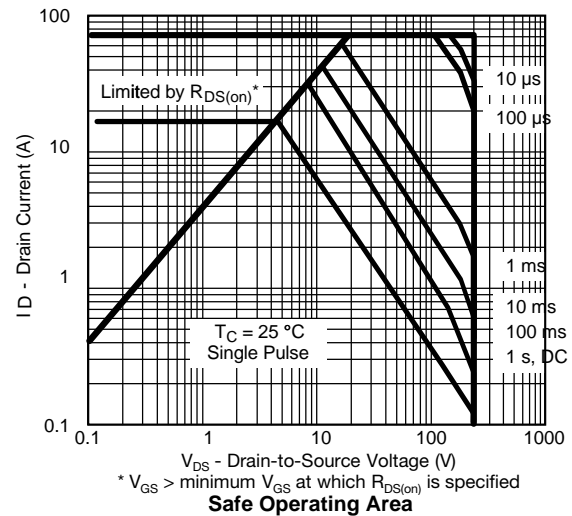


Source-Drain Diode Forward Voltage



Maximum Avalanche Drain Current vs. Case Temperature

On-Resistance vs. Junction Temperature



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